

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	274	156/345.12 156/345.13 156/345.16	USPAT	OR	OFF	2003/09/04 10:29
S2	13915	(polishing planariz\$5) same (grind\$3 condition\$3)	USPAT	OR	OFF	2003/09/04 10:30
S3	1270	("chemical mechanical" adj(polishing planariz\$5) same (grind\$3 condition\$3))	USPAT	OR	OFF	2003/09/04 10:32
S4	0	((("chemical mechanical" adj(polishing planariz\$5) same (grind\$3 condition\$3))) same ((analyz\$3 monitor\$3) adj3 (slurry solution))	USPAT	OR	OFF	2003/09/04 10:34
S5	10	((("chemical mechanical" adj(polishing planariz\$5) same (grind\$3 condition\$3))) same ((analyz\$3 monitor\$3) same (slurry solution))	USPAT	OR	OFF	2003/09/04 10:42
S6	3517	("ammonium citrate" "nitric acid") same (cu copper)	USPAT	OR	OFF	2003/09/04 10:48
S7	559	((("ammonium citrate" "nitric acid") same (cu copper)) and (polish\$3 abras\$3 planariz\$5)	USPAT	OR	OFF	2003/09/04 10:49
S8	53	chopra-dinesh.in. meikle-scott.in.	USPAT	OR	OFF	2003/09/04 12:59
S9	1111	micron.as. and (condition\$3 dress\$3) and (analy\$4 monitor\$3)	USPAT	OR	OFF	2003/09/04 13:00
S10	261	micron.as. and (condition\$3 dress\$3) same (analy\$4 monitor\$3)	USPAT	OR	OFF	2003/09/04 14:10
S11	305	(polish\$3 abras\$3) same (gas air) same (spring)	USPAT	OR	OFF	2003/09/04 14:12
S12	2	("chemical mechanical" adj (polish\$3 abras\$3)) same (gas air) same (spring)	USPAT	OR	OFF	2003/09/04 14:32
S13	2422	("chemical mechanical" adj (polish\$3 abras\$3)) same (dry plasma)	USPAT	OR	OFF	2003/09/04 14:17
S14	70	((("chemical mechanical" adj (polish\$3 abras\$3)) same (dry plasma)) and (spring or "pressure releasing")	USPAT	OR	OFF	2003/09/04 14:17
S15	3598	((dry plasma) same (polish\$3 abras\$3 planari\$5))	EPO; JPO; DERWENT	OR	OFF	2003/09/04 14:33
S16	654	((dry plasma) adj5 (polish\$3 abras\$3 planari\$5))	EPO; JPO; DERWENT	OR	OFF	2003/09/04 14:33
S17	143	((((dry plasma) adj5 (polish\$3 abras\$3 planari\$5))) and (wafer semiconductor)	EPO; JPO; DERWENT	OR	OFF	2003/09/04 14:50

S18	11	(((dry plasma) adj5 (polish\$3 abrad\$3 planari\$5))) and (wafer semiconductor) and (spring pressure)	USPAT; EPO; JPO; DERWENT	OR	OFF	2003/09/04 14:51
S19	1138	134/113 134/104.1	USPAT	OR	OFF	2003/09/05 14:41
S20	21	(134/113 134/104.1) and (dress\$3 grind\$3 condition\$3 clean\$3) near5 (pad cloth platen)	USPAT	OR	OFF	2003/09/05 14:41
S21	55	156/345.13.ccls.	USPAT	OR	OFF	2004/01/07 10:48
S22	890	((dress\$3 clean\$3 condition\$3) with (pad cloth)) same (CMP "chemical mechanical")	USPAT	OR	OFF	2004/01/07 12:56
S23	114	(((dress\$3 clean\$3 condition\$3) with (pad cloth)) same (CMP "chemical mechanical")) and ((analy\$3 monitor\$3 test\$3) with (condition\$3 dress\$3 clean\$3))	USPAT	OR	OFF	2004/01/07 12:57
S24	1	"6736926".pn.	USPAT	OR	OFF	2004/08/30 10:27
S25	2529	156/345.13 134/113 134/104.1 156/345.12 451/66 451/443 451/444	USPAT	OR	OFF	2004/08/30 14:25
S26	1090	(156/345.13 134/113 134/104.1 156/345.12 451/66 451/443 451/444) and (dress\$3 clean\$3 rins\$3 wash\$3) with (pad cloth surface)	USPAT	OR	OFF	2004/08/30 10:33
S27	1049	(156/345.13 134/113 134/104.1 156/345.12 451/66 451/443 451/444) and (polish\$3 abrad\$3)	USPAT	OR	OFF	2004/08/30 10:33
S28	508	(156/345.13 134/113 134/104.1 156/345.12 451/66 451/443 451/444) and ((dress\$3 clean\$3 rins\$3 wash\$3) with (pad cloth surface) same (abrad\$3 polish\$3))	USPAT	OR	OFF	2004/08/30 11:40
S29	149	(condition\$3 dress\$3) same (polish\$3 abrad\$3) same ((monitor\$3 sens\$3 detect\$3 measur\$3) with(torqu\$3 force))	USPAT	OR	OFF	2004/08/30 14:13
S30	50	(condition\$3 dress\$3) same (polish\$3 abrad\$3) same ((monitor\$3 sens\$3 detect\$3 measur\$3) with(torqu\$3 force))	EPO; JPO; DERWENT	OR	OFF	2004/08/30 14:25
S31	40	(156/345.13 134/113 134/104.1 156/345.12 451/66 451/443 451/444)and ((condition\$3 dress\$3) same (monitor\$3 detect\$3 sens\$3) with (force torqu\$3))	USPAT	OR	OFF	2004/08/30 14:27
S32	70	force same (detect\$3 monitor\$3) same "chemical mechanical"	USPAT	OR	OFF	2005/02/10 13:44